



# Bipolar PNP Bare Die – BTP6999

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## Part Description

The BTP6999 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications.

## Key Parameters:

- VCBO = -50V
- VCEO = -40V
- VEBO = -7.5V
- hFE = 200-550 @ VCE = -2V, IC = -0.5A
- VCE(Sat) = -0.185V @ IC = -5.5A, IB = -550mA
- fT = 152 MHz @ VCE = -10V, IE = 0A
- COBO = 53pF @ VCB = -10V

## Features

Very Low VCE(sat)

## Die Size (Unsawn)

1250µm X 1250µm, 49 Mils X 49 Mils

This is a shortform datasheet only

For the full datasheet

Please contact [sales@siliconsupplies.com](mailto:sales@siliconsupplies.com)

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